v ̈Ω Parameter	ɿ N Symbol	̈Ω Ö Rating	D Ӈ Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current(DC)	$I_D(T_C=25\ )$	275	A
	$I_D(T_C=100\ )$	194	A
Drain Current – Pulsed	I_{DM}	1100	A
Power Dissipation	P_{tot}	263	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 175	ɬ
Continuous-Source Current	I_S	275	A
Single Pulse Avalanche Energy (V_{DD}=50V,L=1.0mH)	E_{AS}	2450	mJ
Thermal resistance, junction - Ambient	R_{JA}	45	ɬ 2 Z
Thermal resistance, junction - case	R_{JC}	0.57	

v ̈Ω Parameter	ɿ N Symbol	⊥⊥ ;ʅ Ţ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ʑ Ö Max	D Ӈ Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250uA, V_{GS}=0V	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, I_D=250uA	2		4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V, V_{GS}=0V			1	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			±100	nA

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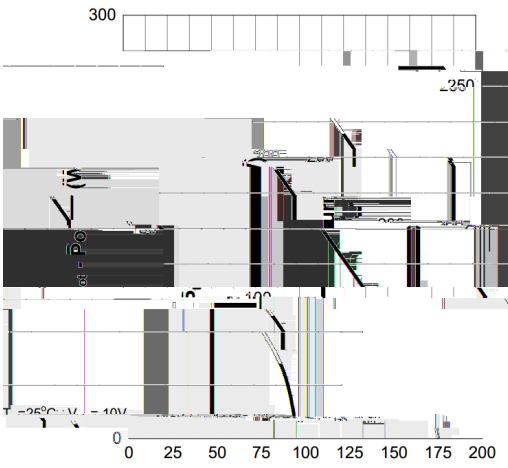
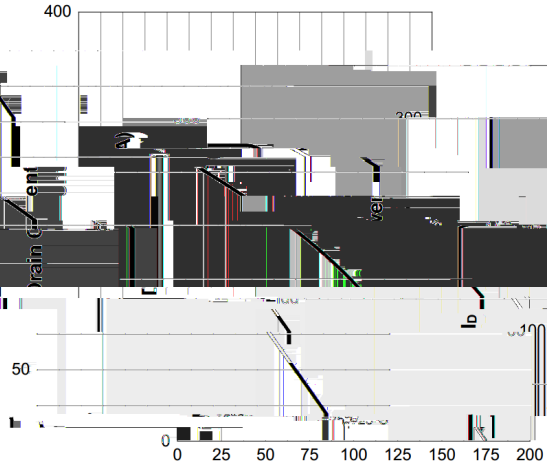


T_J - Junction Temperature (°C)

Fig2. Current Capability



T_J - Junction Temperature (°C)

Fig1. Power Capability

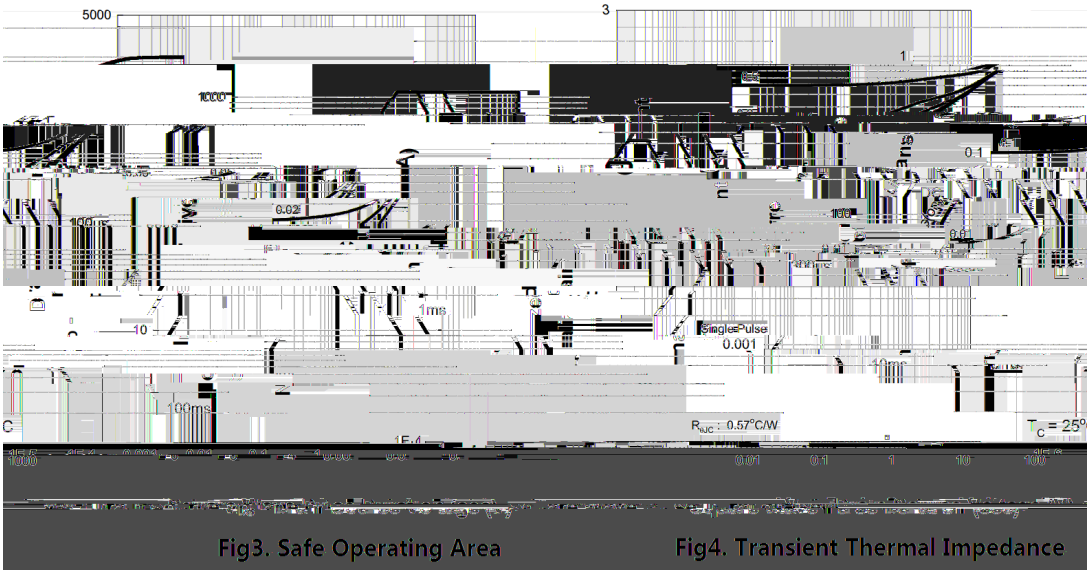
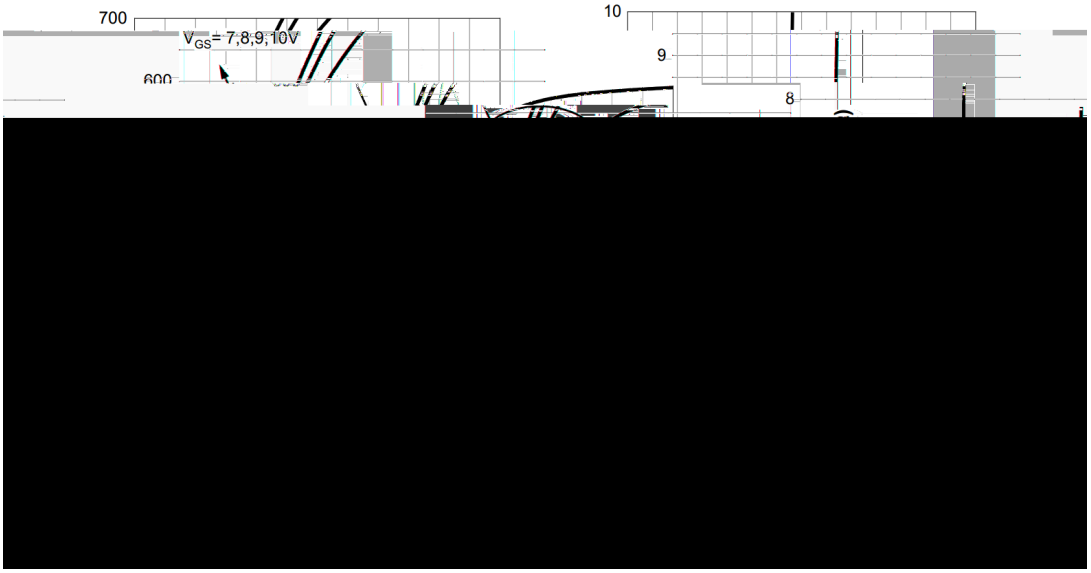


Fig3. Safe Operating Area

Fig4. Transient Thermal Impedance



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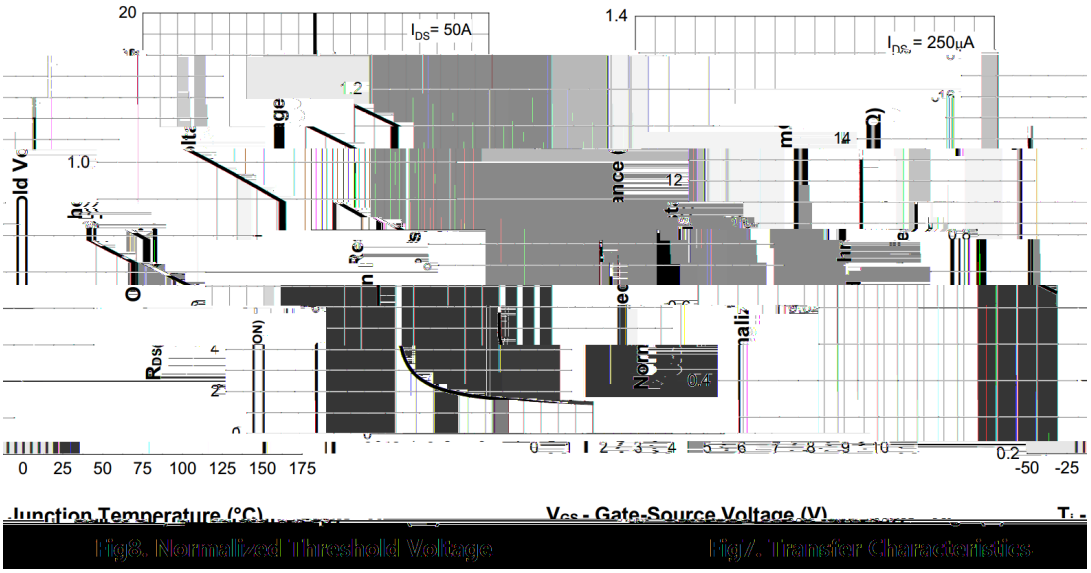

Fig8. Normalized Threshold Voltage Fig7. Transfer Characteristics



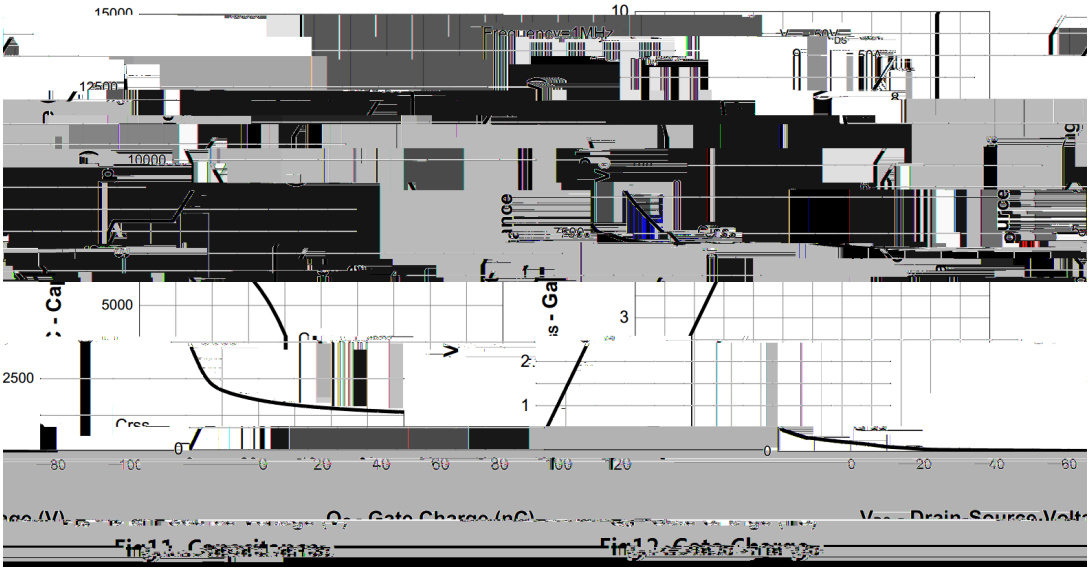

Fig11. Capacitance Fig12. Gate Charge

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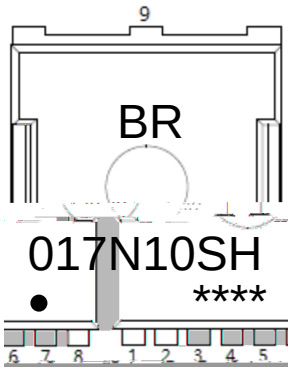
Dimensions In Millimeters
A 2.20 2.30
b2 0.36 0.45 0.55
b3 0.05 0.10 /
b6 3.00
1.20 1.30
9.90 10.00
7.50 7.60
e 1.10
E 9.80
E1 7.40

a g



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